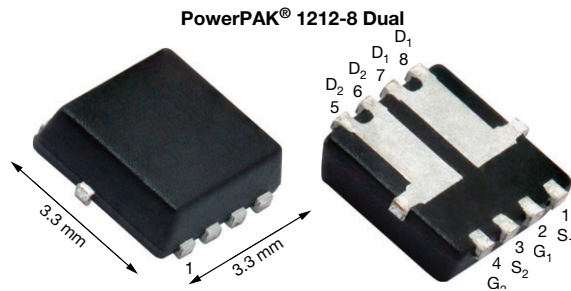


Dual P-Channel 20 V (D-S) MOSFET



PRODUCT SUMMARY	
V_{DS} (V)	-20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V	0.0201
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5$ V	0.0261
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.8$ V	0.0400
Q_g typ. (nC)	15.9
I_D (A) ^{f, g}	6
Configuration	Dual

FEATURES

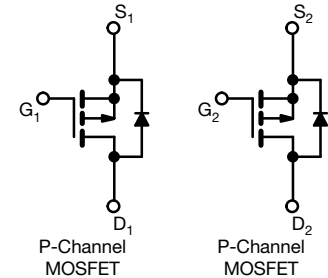
- TrenchFET[®] Gen III p-channel power MOSFET
- 62 % smaller package footprint than SO-8
- Thermally enhanced PowerPAK[®] package
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load switch
- Battery protection
- Adapter and charger switch
- Hand-held and mobile devices



ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiS903DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	-20	V
Gate-source voltage	V_{GS}	± 8	
Continuous drain current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	-6 ^g
		$T_C = 70$ °C	-6 ^g
		$T_A = 25$ °C	-6 ^{a, b, g}
		$T_A = 70$ °C	-6 ^{a, b, g}
Pulsed drain current ($t = 100$ μ s)	I_{DM}	-40	A
Continuous source-drain diode current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	2.2 ^{a, b}
Single pulse avalanche current	I_{AS}	14	mJ
Single pulse avalanche energy	E_{AS}	9.8	
Maximum power dissipation	P_D	$T_C = 25$ °C	23
		$T_C = 70$ °C	14.8
		$T_A = 25$ °C	2.6 ^{a, b}
		$T_A = 70$ °C	1.7 ^{a, b}
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^{c, d}		260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{a, e}	$t \leq 10$ s	R_{thJA}	38	48	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	4.3	5.4	

Notes

- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 94 °C/W
- Based on $T_C = 25$ °C
- Package limited



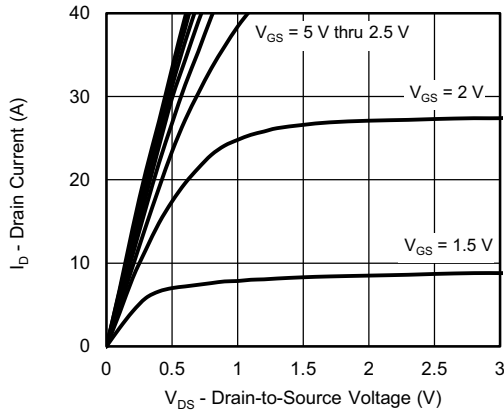
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-20	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-13.7	-	mV/°C
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J		-	-2.6	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.4	-	-1	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V	-	-	± 100	nA
Zero gate voltage drain current	I _{BSS}	V _{DS} = -20 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	
On-state drain current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-10	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V, I _D = -5 A	-	0.0167	0.0201	Ω
		V _{GS} = -2.5 V, I _D = -4 A	-	0.0218	0.0261	
		V _{GS} = -1.8 V, I _D = -2.5 A	-	-	0.0400	
Forward transconductance ^a	g _{fs}	V _{DS} = -1.8 V, I _D = -9.5 A	-	32	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	-	2565	-	pF
Output capacitance	C _{oss}		-	260	-	
Reverse transfer capacitance	C _{rss}		-	240	-	
Total gate charge	Q _g	V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -9.5 A	-	28	42	nC
		V _{DS} = -10 V, V _{GS} = -2.5 V, I _D = -9.5 A	-	15.9	24	
Gate-source charge	Q _{gs}	V _{DS} = -10 V, V _{GS} = -2.5 V, I _D = -9.5 A	-	3.5	-	
Gate-drain charge	Q _{gd}		-	5.6	-	
Gate resistance	R _g	f = 1 MHz	2.22	11.1	22.2	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = -10 V, R _L = 1.3 Ω I _D ≅ -7.6 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	30	45	ns
Rise time	t _r		-	54	81	
Turn-off delay time	t _{d(off)}		-	135	203	
Fall time	t _f		-	63	95	
Turn-on delay time	t _{d(on)}	V _{DD} = -10 V, R _L = 1.3 Ω I _D ≅ -7.6 A, V _{GEN} = -8 V, R _g = 1 Ω	-	12	20	
Rise time	t _r		-	33	50	
Turn-off delay time	t _{d(off)}		-	160	240	
Fall time	t _f		-	60	90	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	6 °	A
Pulse diode forward current	I _{SM}		-	-	40	
Body diode voltage	V _{SD}	I _S = -7.6 A, V _{GS} = 0 V	-	0.8	1.2	V
Body diode reverse recovery time	t _{rr}	I _F = -7.6 A, di/dt = 100 A/μs, T _J = 25 °C	-	26	40	ns
Body diode reverse recovery charge	Q _{rr}		-	16	24	nC
Reverse recovery fall time	t _a		-	12	-	ns
Reverse recovery rise time	t _b		-	14	-	

Notes

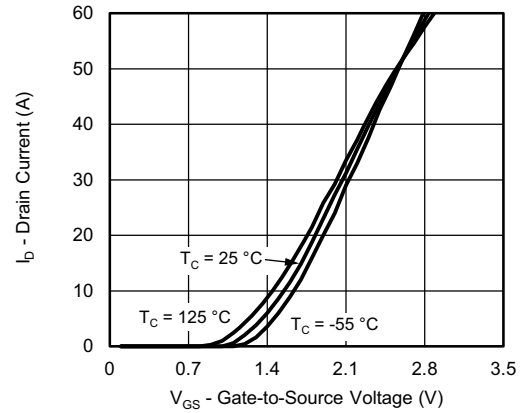
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing
- c. Package limited

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

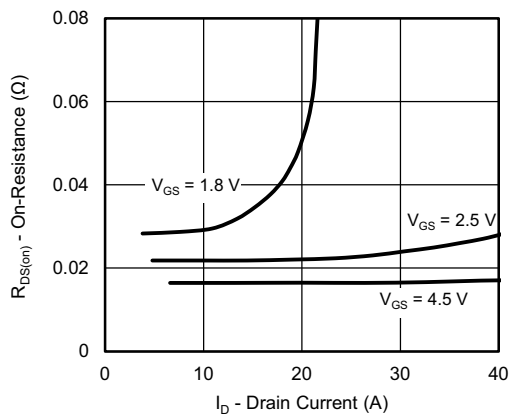
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



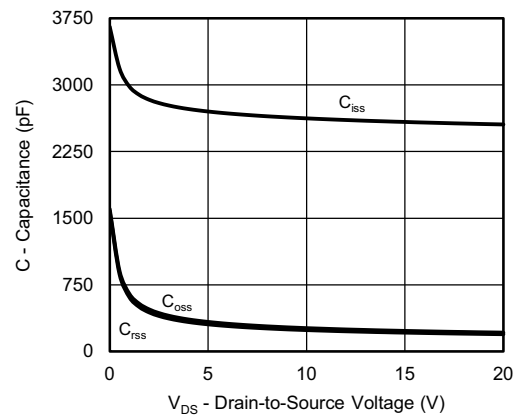
Output Characteristics



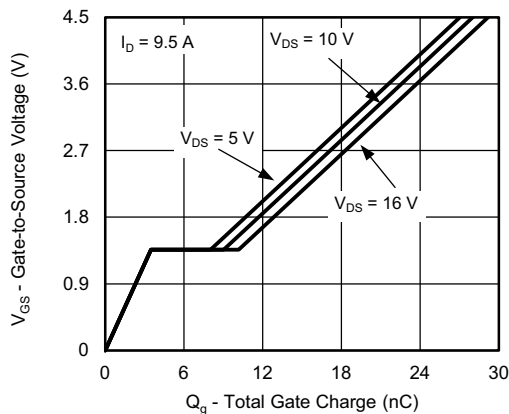
Transfer Characteristics



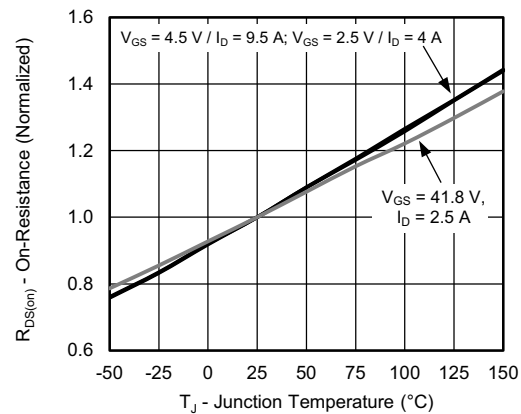
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



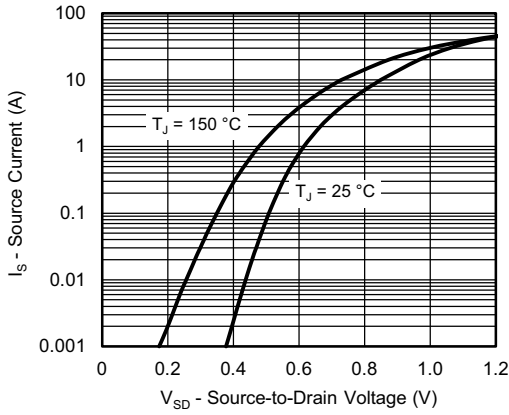
Gate Charge



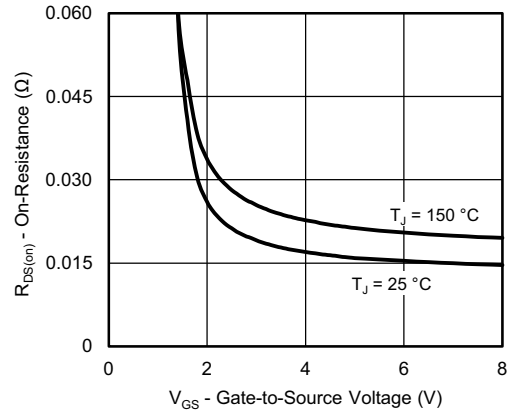
On-Resistance vs. Junction Temperature



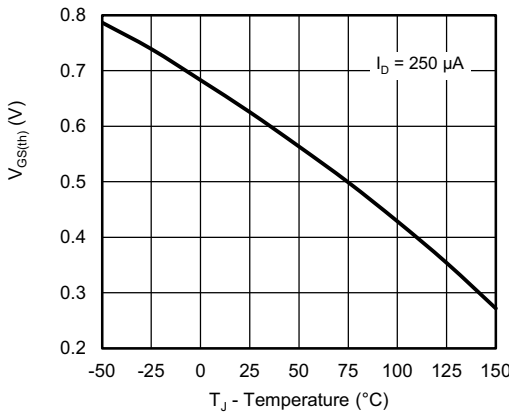
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



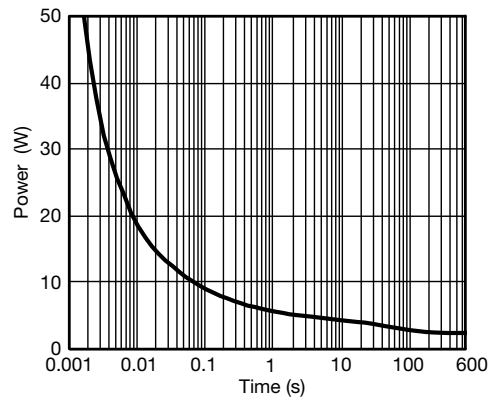
Source-Drain Diode Forward Voltage



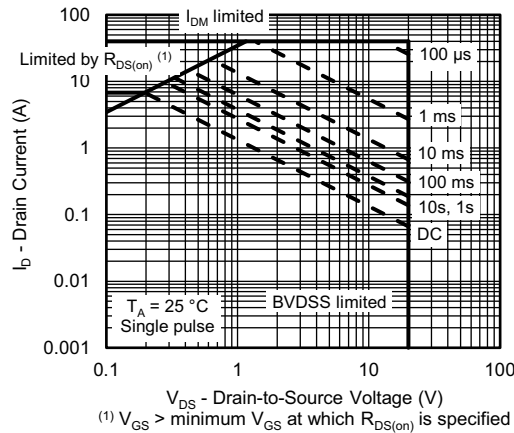
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



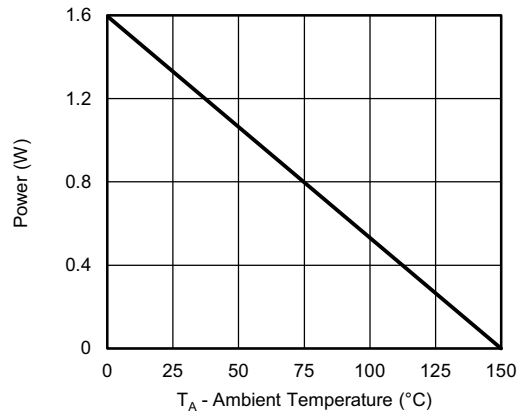
Single Pulse Power, Junction-to-Ambient



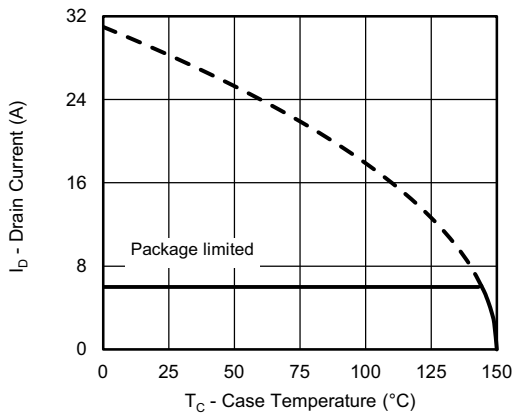
Safe Operating Area, Junction-to-Ambient



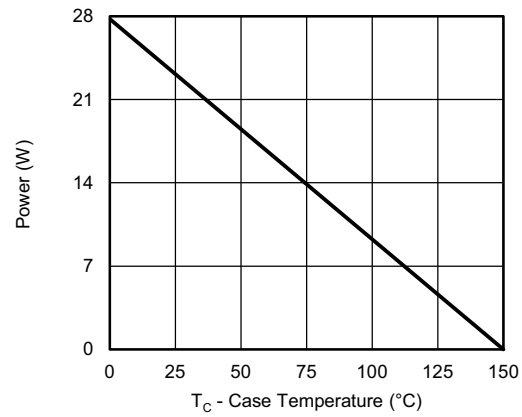
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Power Junction to Ambient



Current Derating ^a



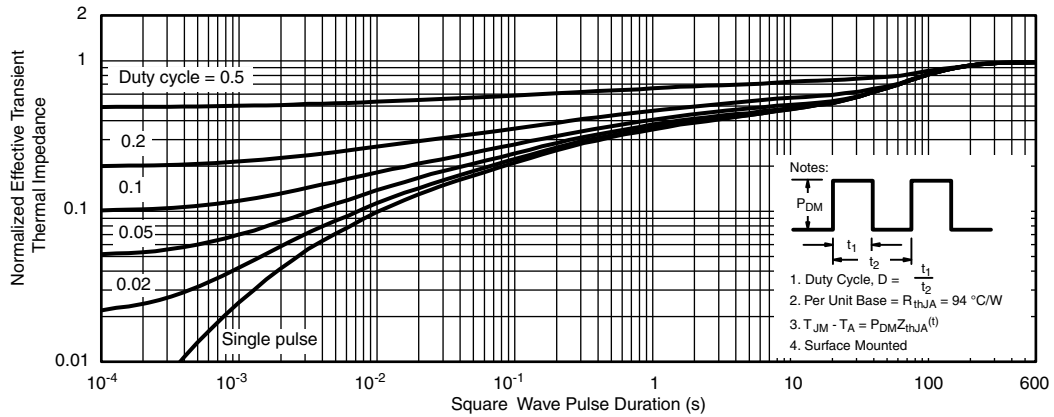
Power Derating

Note

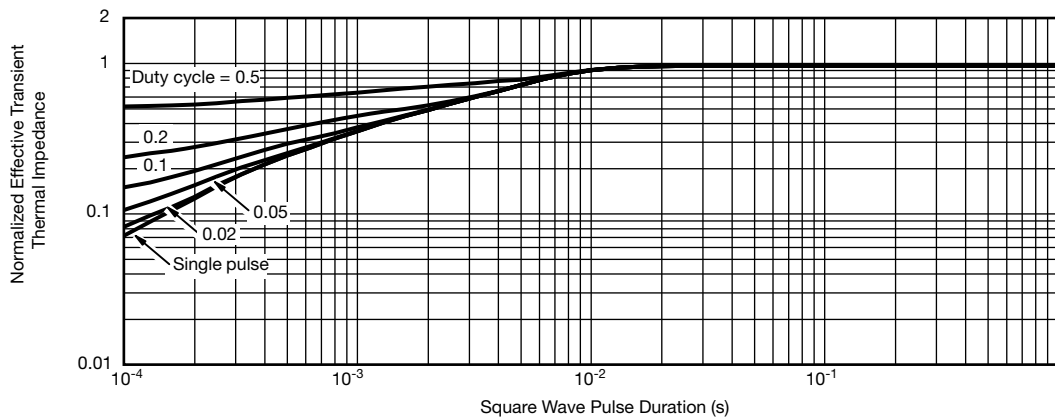
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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